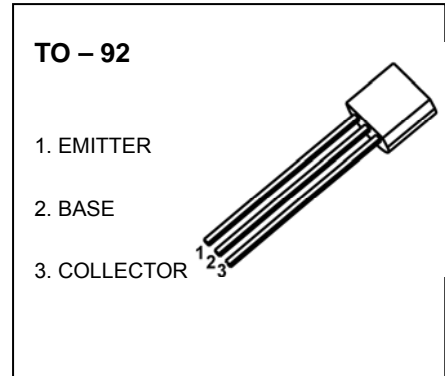


## TO-92 Plastic-Encapsulate Transistors

### 2N5401 TRANSISTOR (PNP)

#### FEATURES

- Switching and Amplification in High Voltage
- Applications such as Telephony
- Low Current
- High Voltage



#### MAXIMUM RATINGS ( $T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CB0}$	Collector-Base Voltage	-160	V
$V_{CEO}$	Collector-Emitter Voltage	-150	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current	-0.6	A
$P_C$	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	200	$^{\circ}\text{C}/\text{W}$
$T_j$	Junction Temperature	150	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature	-55~+150	$^{\circ}\text{C}$

#### ELECTRICAL CHARACTERISTICS ( $T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -0.1\text{mA}, I_E = 0$	-160			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -0.01\text{mA}, I_C = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -120\text{V}, I_E = 0$			-50	nA
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -3\text{V}, I_C = 0$			-50	nA
DC current gain	$h_{FE}$	$V_{CE} = -5\text{V}, I_C = -1\text{mA}$	50			
		$V_{CE} = -5\text{V}, I_C = -10\text{mA}$	60		300	
		$V_{CE} = -5\text{V}, I_C = -50\text{mA}$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50\text{mA}, I_B = -5\text{mA}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -50\text{mA}, I_B = -5\text{mA}$			-1	V
Transition frequency	$f_T$	$V_{CE} = -5\text{V}, I_C = -10\text{mA}, f = 30\text{MHz}$	100		300	MHz

# Typical Characteristics

# 2N5401

